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# HSM221C

Silicon Epitaxial Planar Diode for High Speed Switching

# HITACHI

ADE-208-028C (Z)  
Rev. 3

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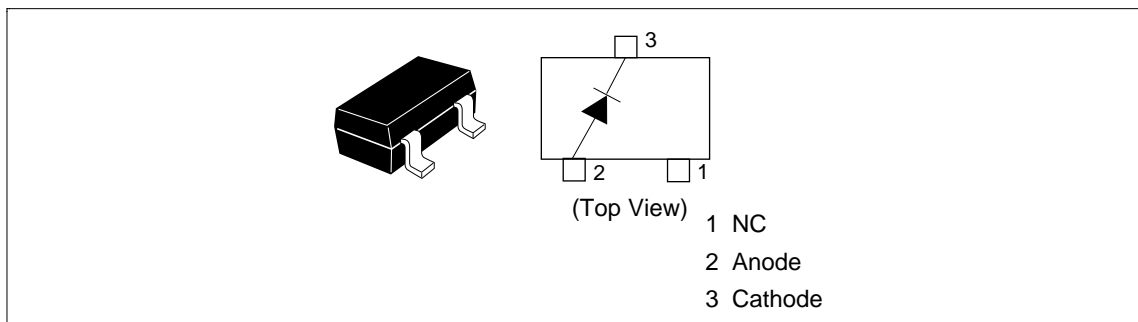
## Features

- Low capacitance, proof against high voltage.
- Fast recovery time.
- MPAK package is suitable for high density surface mounting and high speed assembly.

## Ordering Information

Type No.	Laser Mark	Package Code
HSM221C	A2	MPAK

## Pin Arrangement



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## HSM221C

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### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	85	V
Reverse voltage	$V_R$	80	V
Peak forward current	$I_{FM}$	300	mA
Non-Repetitive peak forward surge current	$I_{FSM}^*$	4	A
Average forward current	$I_O$	100	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: Within 1μs forward surge current.

### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	—	0.76	1.0	V	$I_F = 10mA$
	$V_{F2}$	—	0.88	1.0		$I_F = 50mA$
	$V_{F3}$	—	0.97	1.2		$I_F = 100mA$
Reverse current	$I_R$	—	—	0.1	μA	$V_R = 80V$
Capacitance	C	—	0.5	2.0	pF	$V_R = 0V, f = 1MHz$
Reverse recovery time	$t_{rr}$	—	—	3.0	ns	$I_F = 10mA, V_R = 6V, R_L = 50\Omega$

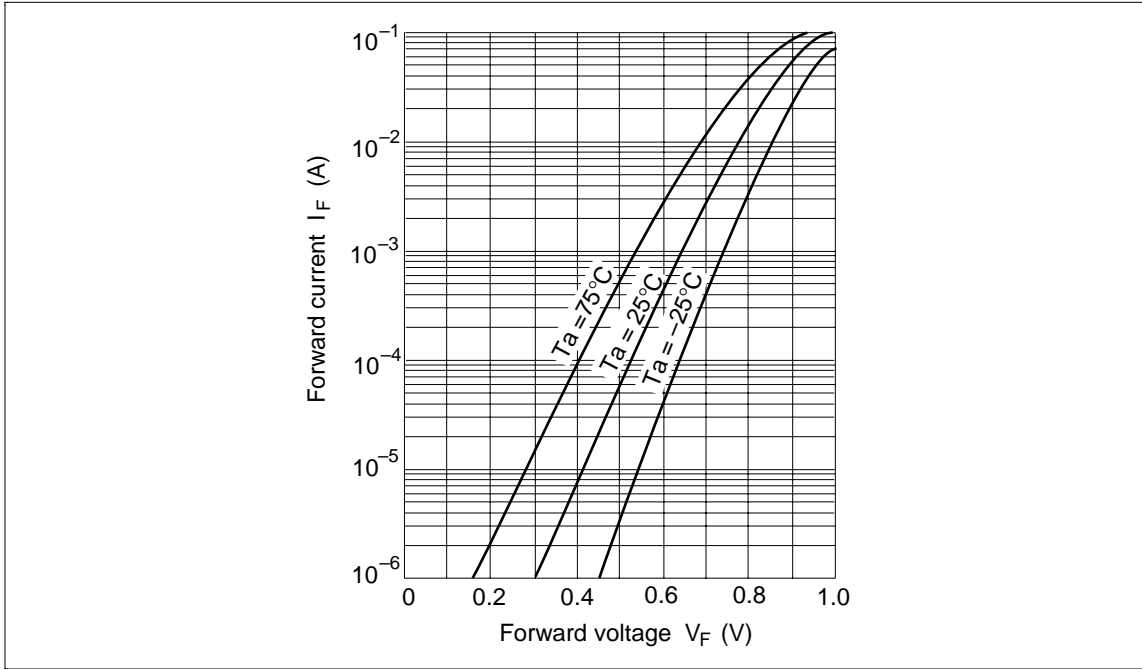


Fig.1 Forward current Vs. Forward voltage

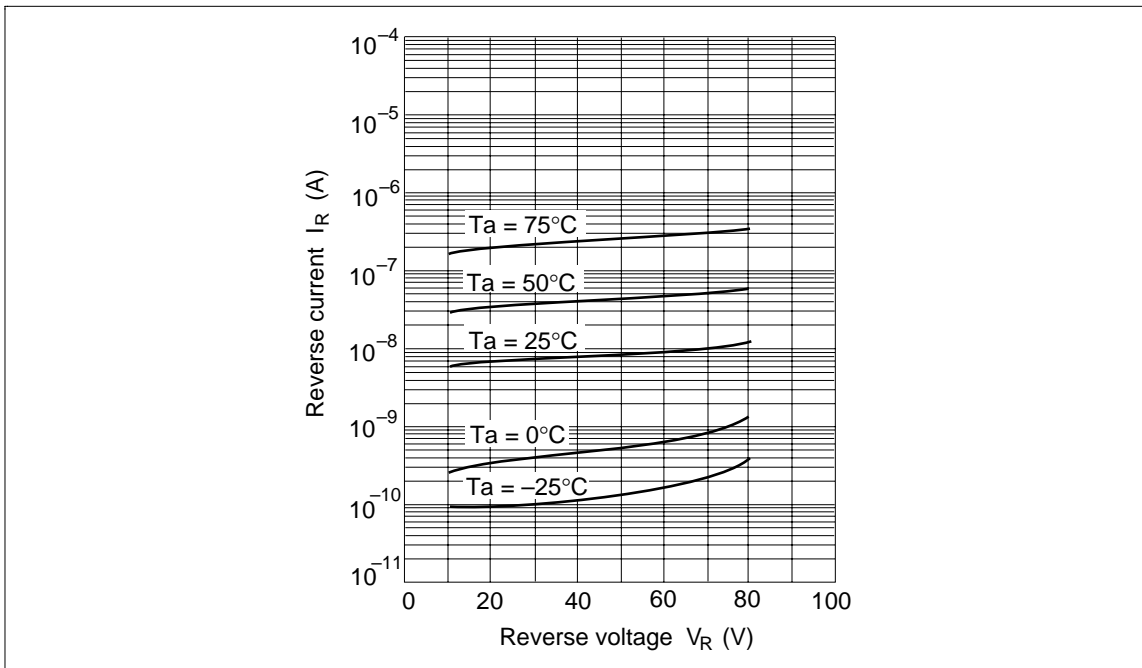


Fig.2 Reverse current Vs. Reverse voltage

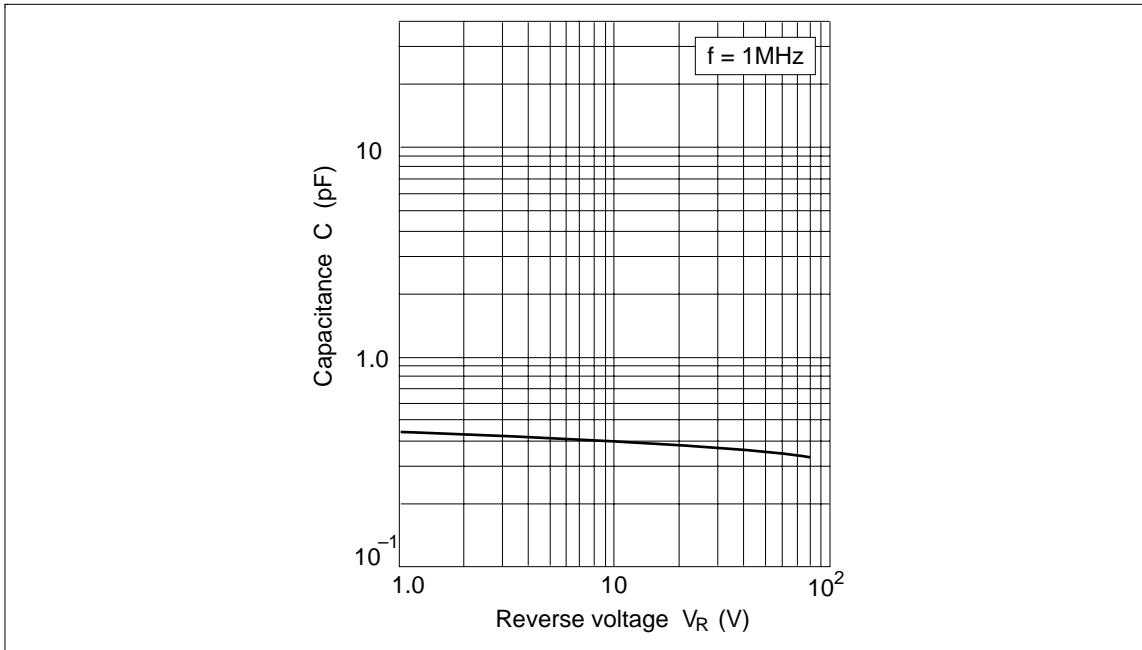


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

